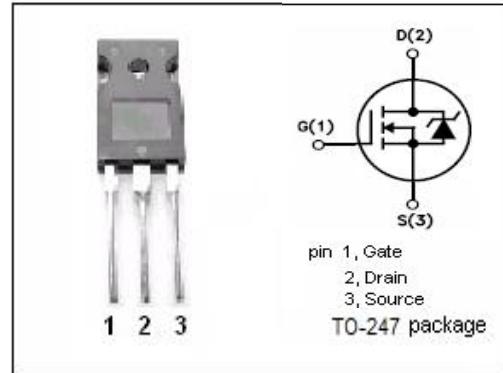


Isc N-Channel MOSFET Transistor

STW45NM60

• FEATURES

- High dv/dt and avalanche capabilities
- Low input capacitance and gate charge
- Low gate input resistance
- 100% avalanche tested
- Tight process control and high manufacturing yields
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



• APPLICATIONS

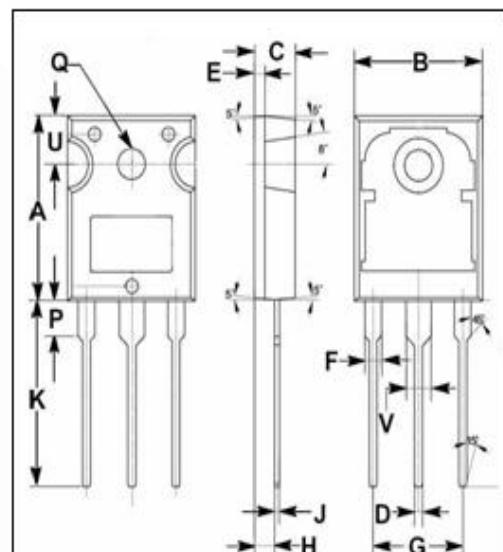
- Switching application

• ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	600	V
V_{GSS}	Gate-Source Voltage	± 30	V
I_D	Drain Current-Continuous@ $T_c=25^\circ\text{C}$ $T_c=100^\circ\text{C}$	45 28	A
I_{DM}	Drain Current-Single Pulsed	180	A
P_D	Total Dissipation	417	W
T_{ch}	Max. Operating Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-65~150	$^\circ\text{C}$

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(ch-c)}$	Channel-to-case thermal resistance	0.3	$^\circ\text{C}/\text{W}$
$R_{th(ch-a)}$	Channel-to-ambient thermal resistance	30	$^\circ\text{C}/\text{W}$



DIM	mm	
	MIN	MAX
A	19.80	20.20
B	15.40	15.80
C	4.90	5.10
D	0.90	1.10
E	1.40	1.60
F	1.90	2.10
G	10.80	11.00
H	2.40	2.60
J	0.50	0.70
K	19.50	20.50
P	3.90	4.10
Q	3.30	3.50
U	5.20	5.40
V	2.90	3.10

Isc N-Channel MOSFET Transistor**STW45NM60****ELECTRICAL CHARACTERISTICS** $T_c=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage	$\text{V}_{\text{GS}}=0\text{V}; \text{I}_D= 0.25\text{mA}$	600			V
$\text{V}_{\text{GS(th)}}$	Gate Threshold Voltage	$\text{V}_{\text{DS}}= \pm 30\text{V}; \text{I}_D=0.25\text{mA}$	3		5	V
$\text{R}_{\text{DS(on)}}$	Drain-Source On-Resistance	$\text{V}_{\text{GS}}= 10\text{V}; \text{I}_D=22.5\text{A}$		90	110	$\text{m}\Omega$
I_{GSS}	Gate-Source Leakage Current	$\text{V}_{\text{GS}}= \pm 30\text{V}; \text{V}_{\text{DS}}= 0\text{V}$			± 0.1	μA
I_{DSS}	Drain-Source Leakage Current	$\text{V}_{\text{DS}}= 600\text{V}; \text{V}_{\text{GS}}= 0\text{V}; \text{T}_J=25^\circ\text{C}$ $\text{T}_J=125^\circ\text{C}$			10 100	μA
V_{SDF}	Diode forward voltage	$\text{I}_{\text{SD}}=45\text{A}, \text{V}_{\text{GS}} = 0 \text{ V}$			1.5	V